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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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BF421

SMALL SIGNAL PNP TRANSISTOR

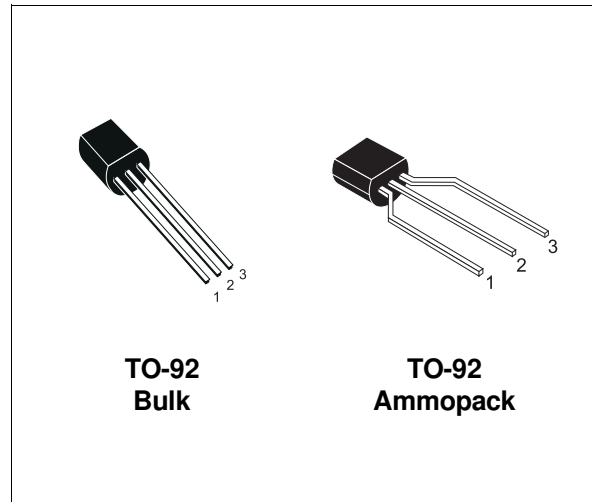
PRELIMINARY DATA

Ordering Code	Marking	Package / Shipment
BF421	BF421	TO-92 / Bulk
BF421-AP	BF421	TO-92 / Ammopack

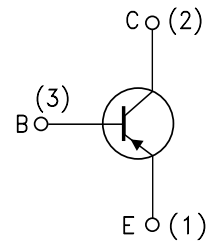
- SILICON EPITAXIAL PLANAR PNP HIGH VOLTAGE TRANSISTOR
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- THE NPN COMPLEMENTARY TYPE IS BF420

APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-300	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-300	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-500	mA
I_{CM}	Collector Peak Current ($t_p < 5ms$)	-600	mA
P_{tot}	Total Dissipation at $T_C = 25^\circ C$	830	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature	150	$^\circ C$

BF421

THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	150	$^{\circ}\text{C}/\text{W}$
$R_{thj-Case}$	Thermal Resistance Junction-Case	Max	50	$^{\circ}\text{C}/\text{W}$

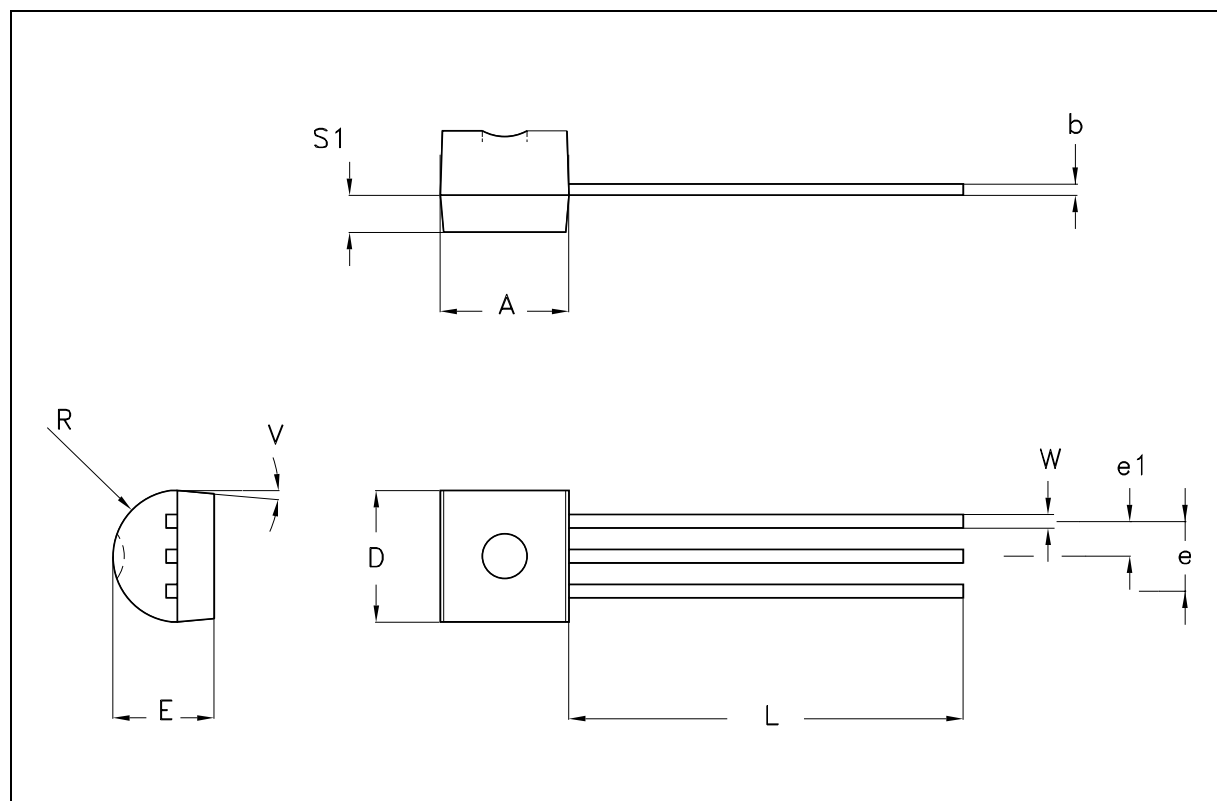
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = -200\text{ V}$ $V_{CB} = -200\text{ V}$ $T_C = 150^{\circ}\text{C}$ $V_{CB} = -300\text{ V}$			-10 -10 -100	nA μA μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = -5\text{ V}$			-50	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -10\text{ mA}$	-300			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -10\text{ }\mu\text{A}$	-300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = -100\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -30\text{ mA}$ $I_B = -5\text{ mA}$			-0.6	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = -30\text{ mA}$ $I_B = -5\text{ mA}$			-1.2	V
h_{FE}^*	DC Current Gain	$I_C = -25\text{ mA}$ $V_{CE} = -20\text{ V}$	50			
f_T	Transition Frequency	$I_C = -10\text{ mA}$ $V_{CE} = -10\text{ V}$ $f = 100\text{ MHz}$	60			MHz
C_{RE}	Reverse Capacitance	$I_E = 0$ $V_{CB} = -30\text{ V}$ $f = 1\text{ MHz}$			1.6	pF

* Pulsed: Pulse duration $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

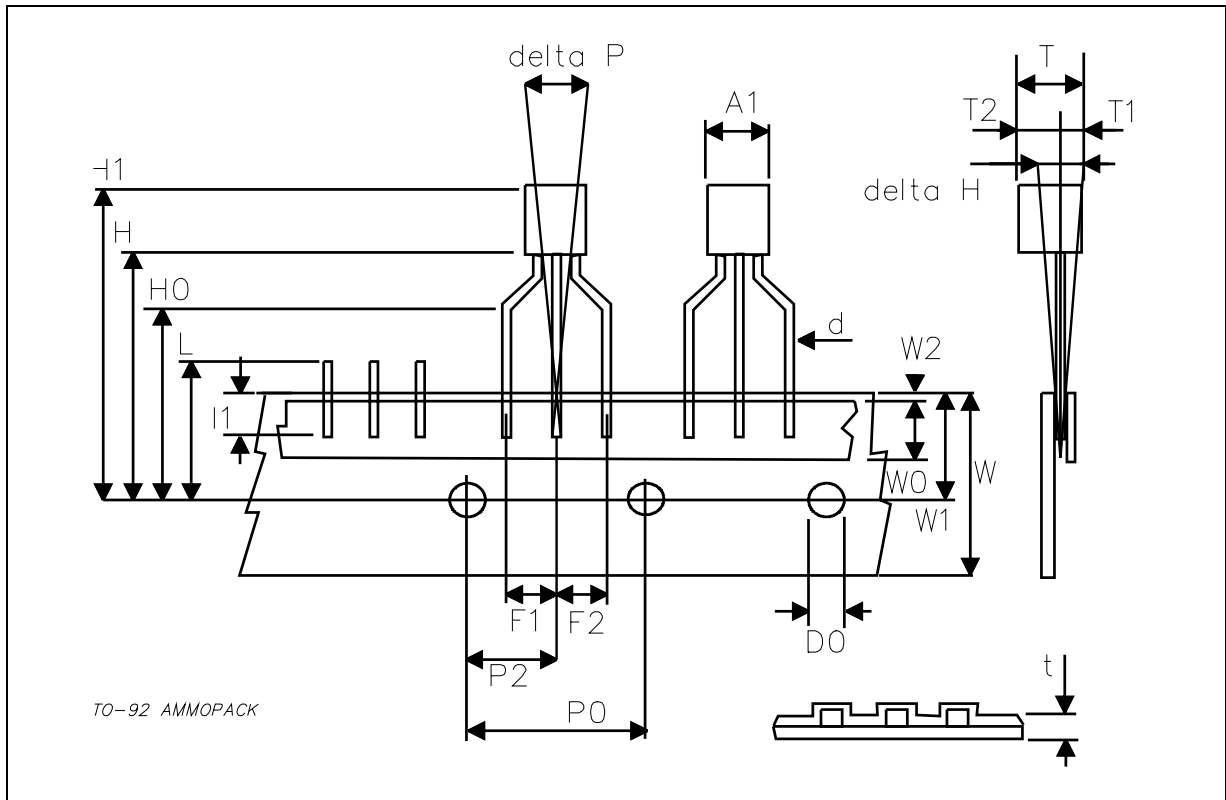
TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A1			4.80			0.189
T			3.80			0.150
T1			1.60			0.063
T2			2.30			0.091
d			0.48			0.019
P0	12.50	12.70	12.90	0.492	0.500	0.508
P2	5.65	6.35	7.05	0.222	0.250	0.278
F1,F2	2.44	2.54	2.94	0.096	0.100	0.116
delta H	-2.00		2.00	-0.079		0.079
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.70	6.00	6.30	0.224	0.236	0.248
W1	8.50	9.00	9.25	0.335	0.354	0.364
W2			0.50			0.020
H	18.50		20.50	0.728		0.807
H0	15.50	16.00	16.50	0.610	0.630	0.650
H1			25.00			0.984
D0	3.80	4.00	4.20	0.150	0.157	0.165
t			0.90			0.035
L			11.00			0.433
I1	3.00			0.118		
delta P	-1.00		1.00	-0.039		0.039



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